SILICON DIODE CHIPS
DEVICE NO. : SD-0013(SD-013)

1. Scope :

This specification applies to silicon diode chips,
Device No. SD-0013.

2. Structure :

2-1. Mesa type.
2-2. Electrodes:
P (Anode) Side: Aluminum alloy or gold alloy.
N (Cathode) Side: Gold alloy.

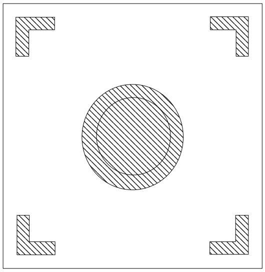
3. Size :

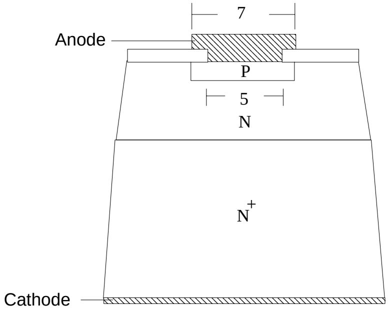
3-1. Chip size: 13 mils × 13 mils (0.330 mm × 0.330 mm).
3-2. Chip Thickness: 7.5 mils ± 1.5 mils (0.191 mm ± 0.038 mm).
3-3. Pattern drawing: Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F=10mA	0.77	0.82	0.87	V
Reverse Current	I_R	V_R=80V		0.5	1.0	μA
Reverse Breakdown Voltage	$V_{(BV)R}$	I_R=5μA	100			V

PATTERN DRAWING
UNIT: mil





5. Packing and labeling :

5-1. Packing :
Two types can be chosen:
PSA : Sheet type
Each pellet is mounted on an adhesive sheet
With wire-bonded electrode side up.
NS : Sheet type
Each pellet is mounted on an adhesive sheet
With back electrode side up.

5-2. Labeling :
Each lot has a label sheet, writting type, lot no,
PCS,avg. Iv, and quantity of good chips.